

CNA1012K (ON1114)

Photo Interrupter

For contactless SW, object detection

Overview

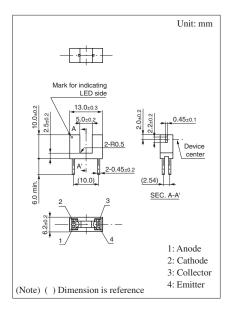
CNA1012K is a photocoupler in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

■ Features

- Highly precise position detection: 0.3 mm
- Wide gap between emitting and detecting elements, suitable for thick plate detection
- Fast response: t_r , $t_f = 6 \mu s$ (typ.)
- Small output current variation against change in temperature
- Large output current

■ Absolute Maximum Ratings $T_a = 25$ °C

	Symbol	mbol Rating			
Input (Light	Reverse voltage	V_R	3	V	
emitting diode)	Forward current	I_F	50	mA	
	Power dissipation *1	P_{D}	75	mW	
Output (Photo	Collector-emitter voltage	V _{CEO}	30	V	
transistor)	(Base open)				
	Emitter-collector voltage	V _{ECO}	5	V	
	(Base open)				
	Collector current	I_C	20	mA	
	Collector power dissipation *2	P_{C}	100	mW	
Temperature	Operating ambient temperature	Topr	-25 to +85	°C	
	Storage temperature	T _{stg}	-30 to +100	°C	



Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C.

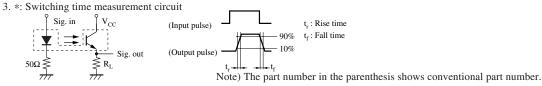
*2: Output power derating ratio is 1.34 mW/°C at $T_a \ge 25$ °C.

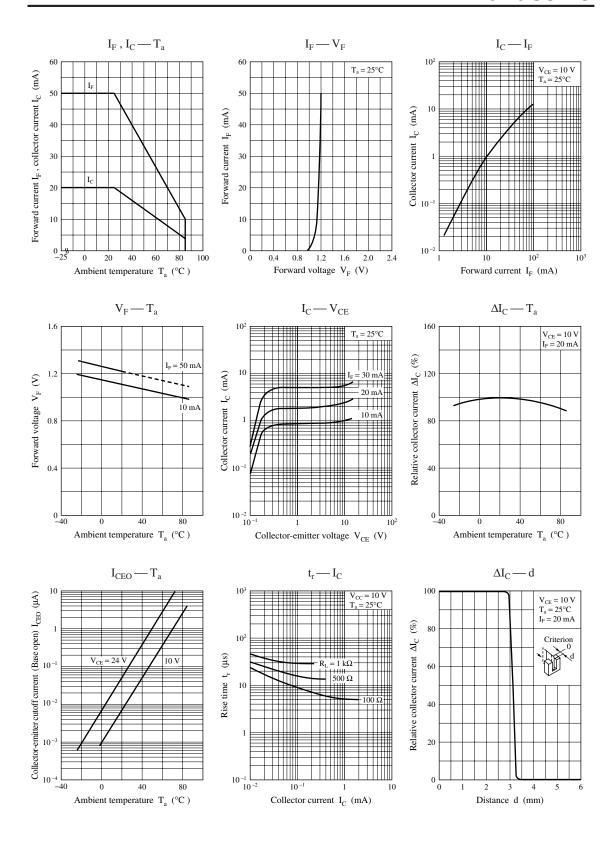
■ Electrical-Optical Characteristics $T_a = 25$ °C ± 3 °C

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	V_F	$I_F = 50 \text{ mA}$		1.2	1.5	V
characteristics	Reverse current	I_R	$V_R = 3 V$			10	μΑ
Output	Collector-emitter cutoff current	I_{CEO}	$V_{CE} = 10 \text{ V}$			200	nA
characteristics	(Base open)						
	Collector-emitter capacitance	C_{C}	$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}$		5		pF
Transfer	Collector current	I_C	$V_{CE} = 10 \text{ V}, I_F = 20 \text{ mA}$	0.7			mA
characteristics	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 50 \text{ mA}, I_C = 0.1 \text{ mA}$			0.3	V
	Rise time *	t _r	$V_{CC} = 10 \text{ V}, I_{C} = 1 \text{ mA}$		6		μs
	Fall time *	t _f	$R_L = 100 \Omega$		6		μs

Note) 1. Input and output are practiced by electricity.

2. This device is designed be disregarded radiation.





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■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

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